

Standard Recipes:

Silicon Nitride:

SiH₄: 1sccm ,NH₃- 20sccm, Tf – 1900°C, Ts – 250 °C

Deposition Rate- 7-8 nm/min

Refractive Index- 1.98-2.0

Intrinsic Polysilicon

SiH₄- 1 sccm, H₂- 20sccm , Tf -1900 °C, Ts- 250 °C

Deposition Rate- 9-10 sccm

Amorphous Silicon

SiH₄- 1sccm, Tf- 1900 °C, Ts-100-150 °C

Deposition Rate- 14-15 nm/min

P-doped Polysilicon

SiH₄- 1sccm, B₂H₆-3.4 sccm, H₂- 20sccm, Tf - 1850 °C, Ts-160 °C

Deposition Rate- 7-8 nm/min

Sheet resistivity- 2.5-3.0 kohm/sq